

SI APD array CHIPS

1. Scope :

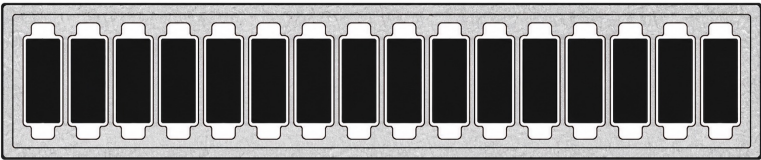
This specification is a surface mount type 16-element SI APD array with high sensitivity in th short wavelength range.

2. Structure :

- Type : 16APD array .
- Electrodes :  
Top side ( Cathode ) : Aluminum alloy. Back side ( Anode ) : Ag.

3. Size :

- Chip size (including scribe line) : (1485 μm x 500 μm)\*16.
- Chip thickness : 250 μm ± 10 μm.
- Bonding pad (Cathode) :100μm x 100μm.



4. Electro-optical characteristics\_one element (Ta = 25 ℃)

| Parameter                  | Symbol      | Condition                                  | Min. | Typ. | Max. | Unit |
|----------------------------|-------------|--------------------------------------------|------|------|------|------|
| Reverse dark Current       | $I_D$       | M=50                                       |      |      | 2    | nA   |
| Reverse breakdown voltage  | $V_{(BR)R}$ | $I_R=10\mu A$                              | 160  |      |      | V    |
| Collector-base Capacitance | $C_{CB}$    | M=50                                       |      |      | 1.0  | pF   |
| Sensitivity                | S           | M=100<br>$\lambda=905nm$                   | 52   | 58   |      | A/W  |
| Rise                       | $T_R$       | M=100<br>$\lambda=905nm$<br>$R_L=50\Omega$ |      | 2    |      | nS   |
| Crosstalk                  |             | M=50                                       | 50   |      |      | dB   |

\*Based on 100% probing

